

# **SEMICONDUCTOR STRUCTURE AND METHOD FOR MANUFACTURING SEMICONDUCTOR STRUCTURE**

## **ABSTRACT**

A semiconductor structure, comprising a substrate (10), word lines (20), a bit line contact plug (30), and a first isolation layer (40). The word lines (20) are located in the substrate (10); a bit line contact hole (11) is provided between two adjacent word lines (20); the bit line contact plug (30) is located in the bit line contact hole (11); the first isolation layer (40) are located on the side wall of the bit line contact hole (11) and covers the side wall of the bit line contact plug (30). Also provided is a method for manufacturing the semiconductor structure, comprising: providing the substrate (10); forming the word lines (20) in the substrate (10), and forming the bit line contact hole (11) between two adjacent word lines (20); forming the first isolation layer (40) on the side wall of the bit line contact hole (11); and forming the bit line contact plug (30) in the first isolation layer (40), the first isolation layer (40) covering the side wall of the bit line contact plug (30). The first isolation layer (40) is provided between the bit line contact plug (30) and the side wall of the bit line contact hole (11), and thus, the coupling effect between the bit line contact plug (30) and the word lines (20) can be reduced, thereby improving the performance of the semiconductor structure.

[Fig. 1]